

N-channel 25 V 1.3 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 2 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

1.4 Quick reference data

Table 1 Quick reference data

- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance
- Power OR-ing
- Server power supplies
- Sync rectifier

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	25	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1] -	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	179	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \\ \text{see } \underline{\text{Figure 12}} \end{array}$	-	1.35	1.7	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \\ \text{see } \underline{\text{Figure } 12} \end{array}$	-	1.05	1.3	mΩ

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Table 1.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ V_{DS} = 12 \text{ V}; \text{ see } \underline{\text{Figure 14}}; \\ \text{see } \underline{\text{Figure 15}} \end{array}$	-	8.3	-	nC
Q _{G(tot)}	total gate charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ V_{DS} = 12 \text{ V}; \text{ see } \underline{\text{Figure 15}}; \\ \text{see } \underline{\text{Figure 14}} \end{array}$	-	31	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		2
2	S	source	mb	
3	S	source		
4	G	gate	Q	
mb	D	mounting base; connected to drain	$\begin{array}{c} 0 \\ 1 \\ 2 \\ 3 \\ 4 \end{array}$	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN1R2-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669			

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
PSMN1R2-25YLC	1C225L

[1] % = placeholder for manufacturing site code.

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5. Limiting values

Table 5. Limiting values

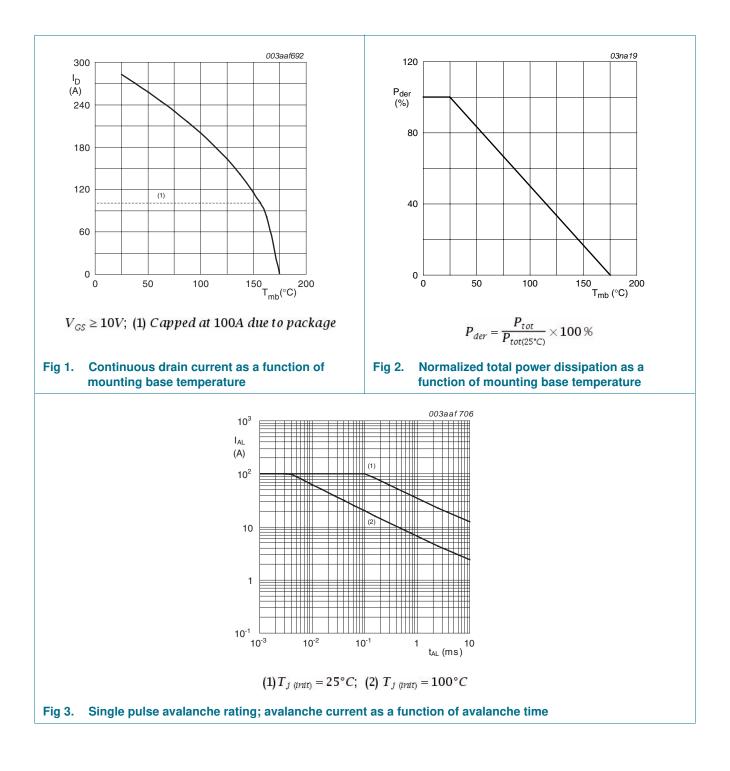
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	25	V
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	25	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	100	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	100	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	1133	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	179	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	690	-	V
Source-drain	n diode				
I _S	source current	T _{mb} = 25 °C	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	1133	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{D} = 100 \text{ A}; \\ V_{sup} \leq 25 \text{ V}; \text{ unclamped}; \text{R}_{GS} = 50 \Omega; \\ \text{see } \underline{\text{Figure 3}} \end{array} $	-	178	mJ

[1] Continuous current is limited by package.

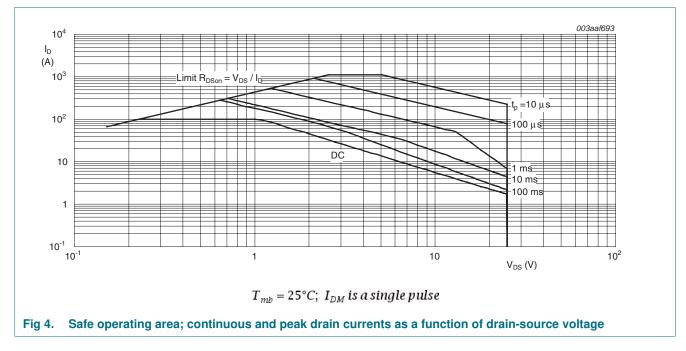
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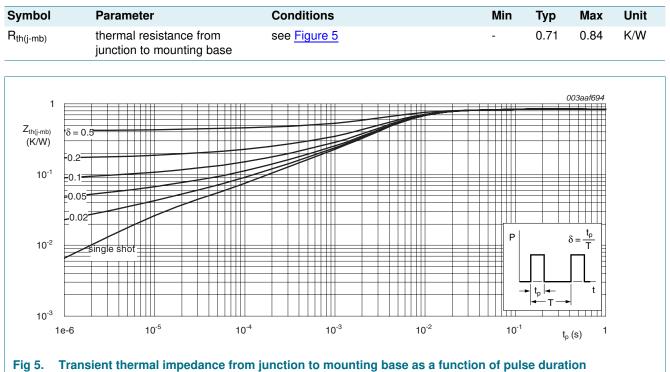
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6. Thermal characteristics

Table 6.Thermal characteristics



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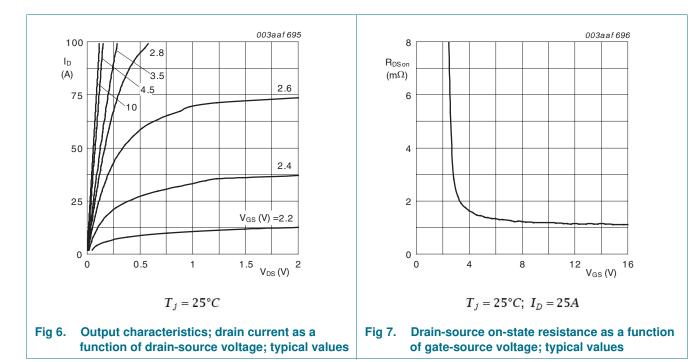
7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS} drain-source		I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	25	-	-	V
()	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _i = -55 °C	22.5	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 10; see Figure 11	1.05	1.45	1.95	V
		I _D = 10 mA; V _{DS} = V _{GS} ; T _i = 150 °C	0.5	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _i = -55 °C	-	-	2.25	V
I _{DSS}	drain leakage current	V _{DS} = 25 V; V _{GS} = 0 V; T _i = 25 °C	-	-	1	μA
		V _{DS} = 25 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
DOON	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	1.35	1.7	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	2.75	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	-	1.05	1.3	mΩ
		$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	2.1	mΩ
R _G	gate resistance	f = 1 MHz	-	1	2	Ω
Dynamic ch	aracteristics					
Q _{G(tot)} total ga	total gate charge	I_D = 25 A; V_{DS} = 12 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	66	-	nC
		I_D = 25 A; V_{DS} = 12 V; V_{GS} = 4.5 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	31	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	65	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	9.7	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	6.7	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	3	-	nC
Q _{GD}	gate-drain charge		-	8.3	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	2.5	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	4173	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	994	-	pF
C _{rss}	reverse transfer capacitance		-	347	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 12 V; R_L = 0.5 Ω ; V_{GS} = 4.5 V;	-	32	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	42	-	ns
t _{d(off)}	turn-off delay time		-	60	-	ns
t _f	fall time		-	29	-	ns
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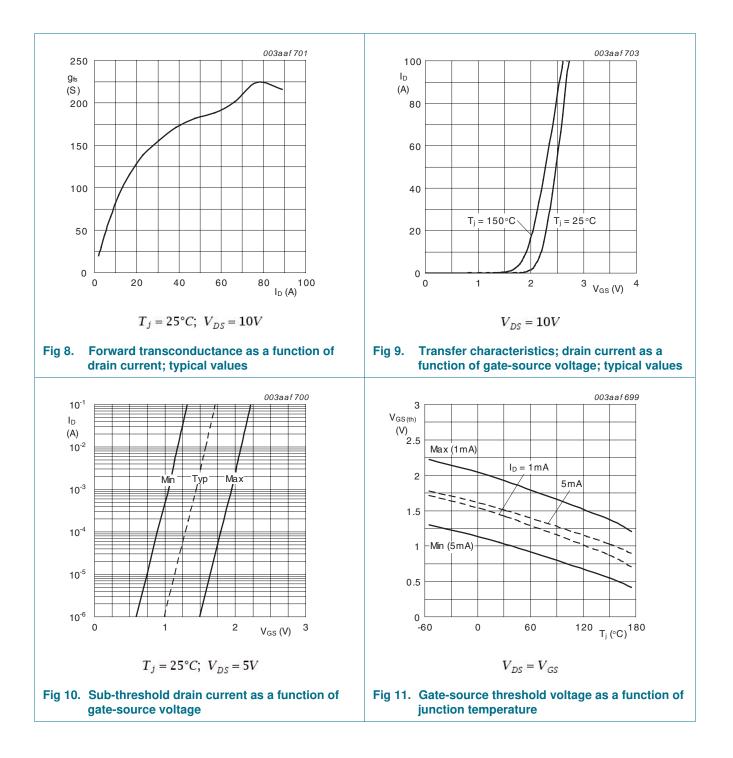
Table 7.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V_{GS} = 0 V; V_{DS} = 12 V; f = 1 MHz; T _j = 25 °C	-	21	-	nC
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.1	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	41	-	ns
Qr	recovered charge	$V_{DS} = 12 V$	-	36	-	nC
t _a	reverse recovery rise time	V_{GS} = 0 V; I _S = 25 A; dI _S /dt = -100 A/µs; V _{DS} = 12 V; see <u>Figure 18</u>	-	24	-	ns
t _b	reverse recovery fall time		-	17	-	ns

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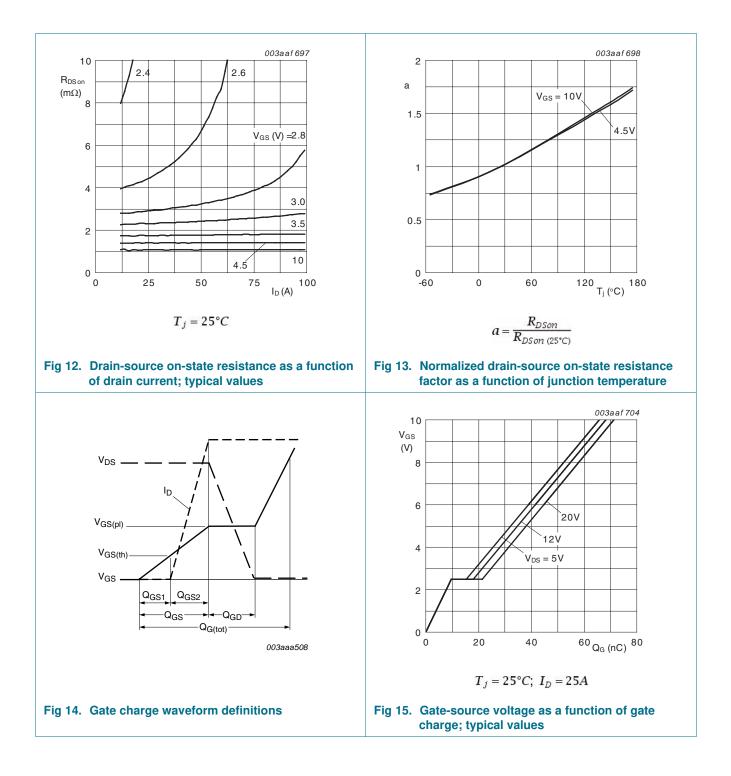
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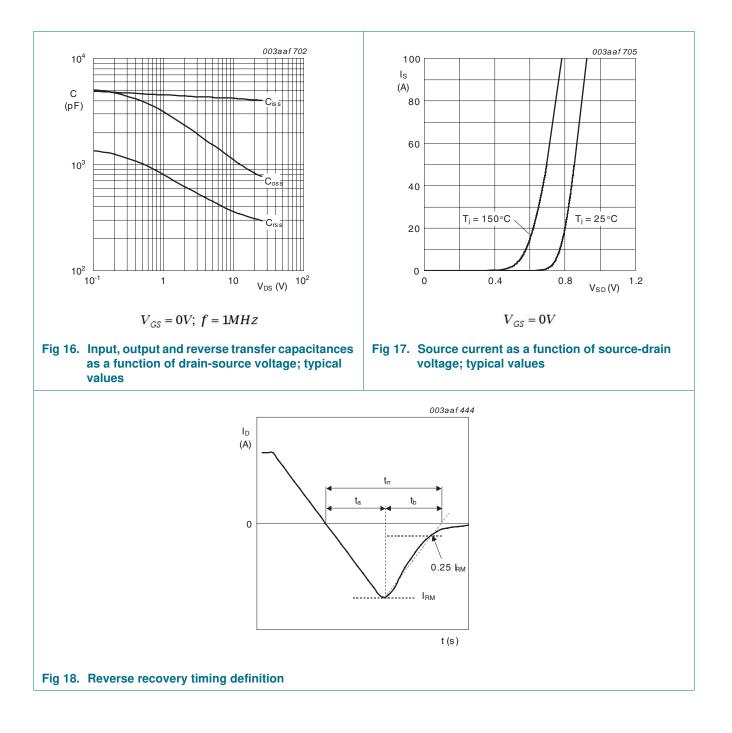
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8. Package outline

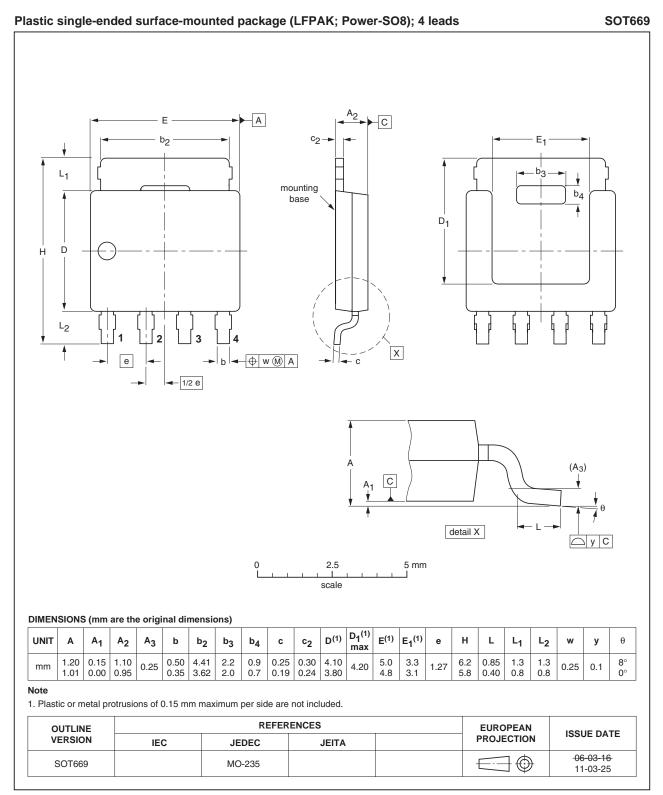


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN1R2-25YLC Product data sheet

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9. Revision history

Table 8. Revision h	8. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PSMN1R2-25YLC v.1	20110502	Product data sheet	-	-	

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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